

### 60V N-Channel MOSFET



**TO-92** 

# **5**

#### **Pin Definition:**

- 1. Source
- 2. Gate
- 3. Drain

#### **PRODUCT SUMMARY**

| V <sub>DS</sub> (V) | $R_{DS(on)}(\Omega)$       | I <sub>D</sub> (mA) |  |  |
|---------------------|----------------------------|---------------------|--|--|
| 60                  | 5 @ V <sub>GS</sub> = 10V  | 100                 |  |  |
|                     | 5.5 @ V <sub>GS</sub> = 5V | 100                 |  |  |

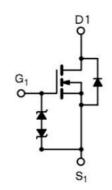
#### **Features**

- Low On-Resistance
- ESD Protection
- High Speed Switching
- Low Voltage Drive

#### **Ordering Information**

| Part No.        | Package | Packing      |
|-----------------|---------|--------------|
| TSM2N7000KCT B0 | TO-92   | 1Kpcs / Bulk |
| TSM2N7000KCT A3 | TO-92   | 2Kpcs / Ammo |

#### **Block Diagram**



N-Channel MOSFET

#### **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

| Parameter  |                                   | Symbol           | Limit       | Unit |  |
|--|-----------------------------------|------------------|-------------|------|--|
| Drain-Source Voltage                             |                                   | $V_{DS}$         | 60          | V    |  |
| Gate-Source Voltage                              |                                   | $V_{GS}$         | ±20         | V    |  |
| Drain Current                                    | Continuous @ T <sub>A</sub> =25°C | I <sub>D</sub>   | 300         | mA   |  |
|  | Pulsed                            | I <sub>DM</sub>  | 700         |      |  |
| Drain Reverse Current                            | Continuous @ T <sub>A</sub> =25°C | I <sub>DR</sub>  | 300         | mA   |  |
|  | Pulsed                            | I <sub>DMR</sub> | 700         |      |  |
| Maximum Power Dissipation                        |                                   | $P_{D}$          | 400         | mW   |  |
| Operating Junction Temperature                   |                                   | TJ               | +150        | °C   |  |
| Operating Junction and Storage Temperature Range |                                   | $T_J, T_STG$     | -55 to +150 | °C   |  |

#### **Thermal Performance**

| Parameter  | Symbol         | Limit | Unit |
|--|----------------|-------|------|
| Lead Temperature (1/8" from case)                    | $T_L$          | 10    | S    |
| Junction to Ambient Thermal Resistance (PCB mounted) | $R\Theta_{JA}$ | 357   | °C/W |

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.



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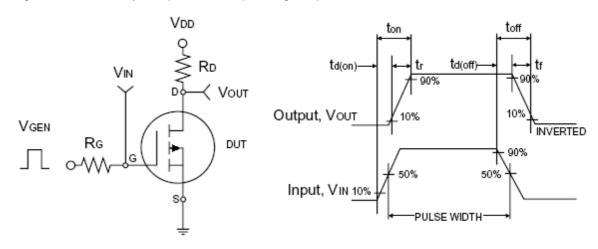


**Electrical Specifications** (Ta = 25°C, unless otherwise noted)

| Parameter  | Conditions                                      | Symbol              | Min | Тур  | Max | Unit |
|--|---|---------------------|-----|------|-----|------|
| Static   |   |                     |     |      |     |      |
| Drain-Source Breakdown Voltage   | $V_{GS} = 0V, I_D = 10\mu A$                    | BV <sub>DSS</sub>   | 60  |      |     | V    |
| Gate Threshold Voltage   | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$            | V <sub>GS(TH)</sub> | 1.0 |      | 2.5 | V    |
| Gate Body Leakage  | $V_{GS} = \pm 20V, V_{DS} = 0V$                 | I <sub>GSS</sub>    |     |      | ±10 | uA   |
| Zero Gate Voltage Drain Current  | $V_{DS} = 60V, V_{GS} = 0V$                     | I <sub>DSS</sub>    |     |      | 1.0 | uA   |
| Danier Courses On Otata Desistance                                       | $V_{GS} = 10V, I_D = 100mA$                     | Б                   |     | 3    | 5   |      |
| Drain-Source On-State Resistance $V_{GS} = 5V, I_D = 100mA$ $R_{DS(ON)}$ |   | 3.6                 | 5.5 | Ω    |     |      |
| Forward Transconductance   | $V_{DS} = 10V, I_{D} = 200mA$                   | g <sub>fs</sub>     | 100 |      |     | mS   |
| Diode Forward Voltage  | $I_S = 300 \text{mA}, V_{GS} = 0 \text{V}$      | V <sub>SD</sub>     |     | 0.9  | 1.2 | V    |
| Dynamic <sup>b</sup>   |   |                     |     |      |     |      |
| Total Gate Charge  | $V_{DS} = 10V, I_D = 250mA,$<br>$V_{GS} = 4.5V$ | $Q_g$               |     | 0.4  |     | nC   |
| Input Capacitance  | $V_{DS} = 25V, V_{GS} = 0V,$                    | C <sub>iss</sub>    |     | 7.32 |     |      |
| Output Capacitance   |   | C <sub>oss</sub>    |     | 3.42 |     | pF   |
| Reverse Transfer Capacitance   | f = 1.0MHz                                      | C <sub>rss</sub>    |     | 7.63 |     |      |
| Switching <sup>c</sup>   |   |                     |     |      |     |      |
| Turn-On Delay Time   | $V_{DD} = 30V, R_{G} = 10\Omega$                | t <sub>d(on)</sub>  |     | 25   |     | C    |
| Turn-Off Delay Time  | $I_D = 100 \text{mA}, V_{GEN} = 10 \text{V},$   | t <sub>d(off)</sub> |     | 35   |     | nS   |

#### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
  b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

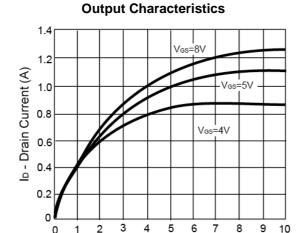
Switchin Waveforms



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#### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



## 1.4 1.2 lo - Drain Current (A) 1.0 0.8 0.6 0.4 0.2

**Transfer Characteristics** 

#### **On-Resistance vs. Drain Current**

4

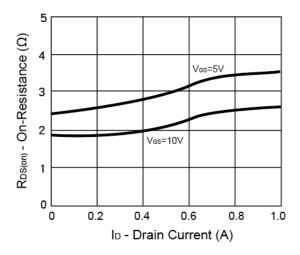
6 7 8

VDS - Drain-to-Source Voltage (V)

10

2

0



#### Forward Transfer Admittance vs. Drain Current

5

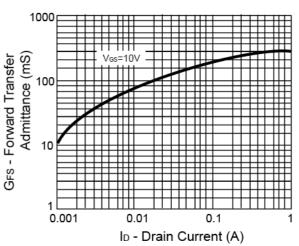
V<sub>GS</sub> - Gate-to-Source Voltage (V)

6 7 8 9 10

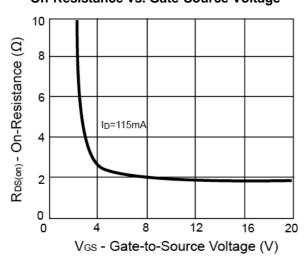
0

0

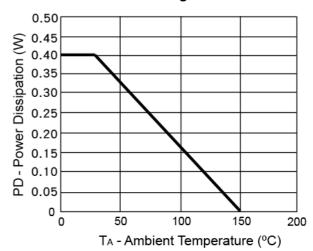
2 3 4



#### On-Resistance vs. Gate-Source Voltage



#### **Power Derating Curve**

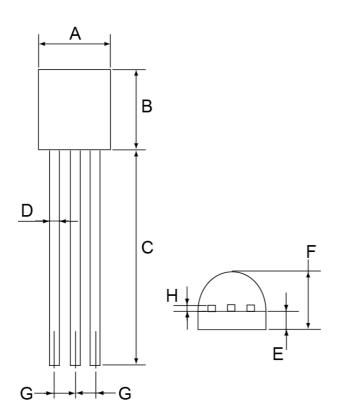








## **TO-92 Mechanical Drawing**



| TO-92 DIMENSION |             |      |             |       |  |
|-----------------|-------------|------|-------------|-------|--|
| DIM             | MILLIMETERS |      | INCHES      |       |  |
|                 | MIN         | MAX  | MIN         | MAX   |  |
| Α               | 4.30        | 4.70 | 0.169       | 0.185 |  |
| В               | 4.30        | 4.70 | 0.169       | 0.185 |  |
| С               | 13.53 (typ) |      | 0.532 (typ) |       |  |
| D               | 0.39        | 0.49 | 0.015       | 0.019 |  |
| Е               | 1.18        | 1.28 | 0.046       | 0.050 |  |
| F               | 3.30        | 3.70 | 0.130       | 0.146 |  |
| G               | 1.27        | 1.31 | 0.050       | 0.051 |  |
| Н               | 0.33        | 0.43 | 0.013       | 0.017 |  |

## **Marking Diagram**



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

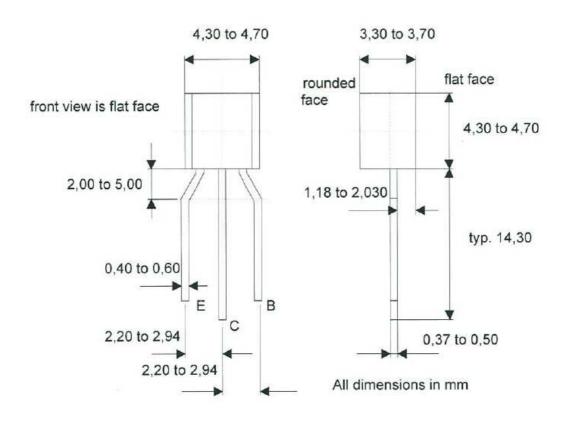
L = Lot Code



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## **TO-92 Ammo Pack Mechanical Drawing**





## TSM2N7000K 60V N-Channel MOSFET

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